

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
 - Class Q Military
 - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.



54FCT/74FCT244 Octal Buffer/Line Driver with TRI-STATE® Outputs

General Description

The 'FCT244 is an octal buffer and line driver designed to be employed as a memory address driver, clock driver and bus-oriented transmitter/receiver which provides improved PC board density.

FACTTM FCT utilizes NSC quiet series technology to provide improved quiet output switching and dynamic threshold performance.

FACT FCT and GTOTM output control and undershoot corrector in addition to a split ground bus for superior performance.

Features

- \blacksquare I_{CC} and I_{OZ} reduced to 40.0 μA and ±2.5 μA respectively
- NSC 54FCT/74FCT244 is pin and functionally equivalent to IDT 54FCT/74FCT244
- Controlled output edge rates and undershoot for improved noise immunity. Internal split ground for improved noise immunity
- Input clamp diodes to limit bus reflections
- TTL/CMOS input and output level compatible
- I_{OL} = 64 mA (commercial) and 48 mA (military)
- CMOS power levels
- ESD immunity ≥ 4 kV typ
- Military product compliant to MIL-STD 883C and standard military drawing #5962-87630

Ordering Code: See Section 8

Logic Symbol

IEEE/IEC

TL/F/10240-1

05

06

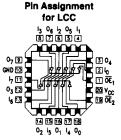
for DIP, Fiatpak and SOIC $\overline{0\overline{E}}_1$, $\overline{1}$, $\overline{0}$, $\overline{0}$

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Pin Assianment

TL/F/10240-2

Connection Diagrams



TL/F/10240-3

Pin Names	Description					
ŌĒ₁, ŌĒ₂	TRI-STATE Output Enable Inputs					
10-17	Inputs					
00-07	Outputs					

Truth Tables

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Inp	uts	Outputs
ŌE ₁	1	(Pins 12, 14, 16, 18)
L	L	L
L	H	н
Н	Х	Z

Inp	uts	Outputs
ŌĒ ₂	Ī	(Pins 3, 5, 7, 9)
L	L	L
L	Н	н
Н	X	Z

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

Z = High Impedance

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Terminal Voltage with Respect to GND (V_{TERM})

54FCT -0.5V to +7.0V 74FCT -0.5V to +7.0V

Temperature under Bias (TBIAS)

74FCT -55°C to +125°C 54FCT -65°C to +135°C

Storage Temperature (T_{STG})

Note 1: Absolute maximum ratings are those values beyond which damage to the device may occur. Exposure to absolute maximum rating conditions for extended periods may affect reliability. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables.

Recommended Operating Conditions

Supply Voltage (V_{CC})

 54FCT
 4.5V to 5.5V

 74FCT
 4.75V to 5.25V

 Input Voltage
 0V to V_{CC}

 Output Voltage
 0V to V_{CC}

Operating Temperature (T_A)

54FCT -55°C to +125°C 74FCT -0°C to +70°C

Junction Temperature (T_J)

CDIP 175°C PDIP 140°C

Note: All commercial packaging is not recommended for applications requiring greater than 2000 temperature cycles from -40° C to $+125^{\circ}$ C.

DC Characteristics for 'FCT Family Devices

Typical values are at $V_{CC}=5.0V$, 25°C ambient and maximum loading. For test conditons shown as Max, use the value specified for the appropriate device type: Com: $V_{CC}=5.0V\pm5\%$, $T_A=0^{\circ}C$ to $+70^{\circ}C$; Mil: $V_{CC}=5.0V\pm10\%$, $T_A=-55^{\circ}C$ to $+125^{\circ}C$, $V_{HC}=V_{CC}-0.2V$

Symbol	Parameter	54FCT/74FCT			Units	Conditions		
OyiiiDO:	r at at note:	Min	Тур	Max	Oilles	Conditions		
V _{IH}	Minimum High Level Input Voltage	2.0			٧			
V _{IL}	Maximum Low Level Input Voltage			0.8	٧			
I _{IH}	Input High Current			5.0 5.0	μΑ	V _{CC} = Max	V _I = V _{CC} V _I = 2.7V (Note 2)	
I _{IL}	Input Low Current			-5.0 -5.0	μΑ	V _{CC} = Max	V _I = 0.5V (Note 2) V _I = GND	
loz	Maximum TRI-STATE Current			2.5 2.5 -2.5 -2.5	μΑ	V _{CC} = Max	$V_O = V_{CC}$ $V_O = 2.7V \text{ (Note 2)}$ $V_O = 0.5V \text{ (Note 2)}$ $V_O = \text{GND}$	
V _{IK}	Clamp Diode Voltage		-0.7	-1.2	٧	$V_{CC} = Min; I_N = -18 \text{ mA}$		
los	Short Circuit Current	-60	-120		mA	V _{CC} = Max (Note 1); V _O = GND		
V _{OH}	Minimum High Level Output Voltage	2.8 V _{HC}	3.0 V _{CC}			$V_{CC} = 3V; V_{IN} = 0.2V$ $V_{CC} = Min$		
		2.4	4.3		V	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -12 \text{ mA (Mil)}$ $I_{OH} = -15 \text{ mA (Com)}$	
V _{OL}	Maximum Low Level		GND	0.2		V _{CC} = 3V; V _{IN} = 0.2V or V _{HC} ; I _{OL} = 300 μ.		
	Output Voltage		GND 0.3 0.3	0.2 0.55 0.55	٧	$V_{CC} = Min$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 300 \mu A$ $I_{OL} = 48 \text{ mA (Mil)}$ $I_{OL} = 64 \text{ mA (Com)}$	
lcc	Maximum Quiescent Supply Current		1.0	40.0	μΑ	$\begin{aligned} & V_{CC} = Max \\ & V_{IN} \geq V_{HC}, V_{IN} \leq 0.2V \\ & f_I = 0 \end{aligned}$		
ΔI _{CC}	Quiescent Supply Current; TTL Inputs HIGH		0.5	2.0	mA	V _{CC} = Max V _{IN} = 3.4V (Note 3)		

DC Characteristics for 'FCT Family Devices (Continued)

Typical values are at $V_{CC}=5.0V$, 25°C ambient and maximum loading. For test conditions shown as Max, use the value specified for the appropriate device type: Com: $V_{CC}=5.0V\pm5\%$, $T_A=0$ °C to +70°C; Mil: $V_{CC}=5.0V\pm10\%$, $T_A=-55$ °C to +125°C, $V_{HC}=V_{CC}-0.2V$

Symbol	Parameter	74FCT			Units	Conditions		
		Min	Тур	Max	Oints	Conditions		
ICCD	Dynamic Power Supply Current (Note 4)	!	0.15	0.55	mA/MHz	V _{CC} = Max Outputs Open $\overline{OE}_1 = \overline{OE}_2 = GND$ One Input Toggling 50% Duty Cycle	V _{IN} ≥ V _{HC} V _{IN} ≤ 0.2V	
lc	Total Power Supply Current (Note 6)		1.5	5.5		V _{CC} = Max Outputs Open $\overline{\text{OE}}_1 = \overline{\text{OE}}_2 = \text{GND}$	V _{IN} ≥ V _{HC} V _{IN} ≤ 0.2V	
			1.8	6.0	mA.	f _I = 10 MHz One Bit Toggling 50% Duty Cycle	V _{IN} = 3.4V V _{IN} = GND	
			3.0	9.0		(Note 5) V _{CC} = Max Outputs Open $\overline{OE}_1 = \overline{OE}_2 = GND$	V _{IN} ≥ V _{HC} V _{IN} ≤ 0.2V	
			5.0	14.5		f _i = 2.5 MHz Eight Bits Toggling 50% Duty Cycle	V _{IN} = 3.4V V _{IN} = GND	

Note 1: Maximum test duration not to exceed one second, not more than one output shorted at one time.

Note 2: This parameter guaranteed but not tested.

Note 3: Per TTL driven input (VIN = 3.4V); all other inputs at VCC or GND.

Note 4: This parameter is not directly testable, but is derived for use in Total Power Supply calculations.

Note 5: Values for these conditions are examples of the I_{∞} formula. These limits are guaranteed but not tested.

Note 6: IC = IQUIESCENT + INPUTS + IDYNAMIC

 $i_C = i_{CC} + \Delta i_{CC} D_H N_T + i_{CCD} (f_{CP}/2 + f_I N_I)$

ICC = Quiescent Current

ΔI_{CC} = Power Supply Current for a TTL High Input (V_{IN} = 3.4V)

DH = Duty Cycle for TTL Inputs High

N_T = Number of inputs at D_H

I_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)

f_{CP} = Clock Frequency for Register Devices (Zero for Non-Register Devices)

f₁ = Input Frequency

N_I = Number of Inputs at f

All currents are in milliamps and all frequencies are in megahertz.

Note 7: For 54FCT, $l_{CCD} = 0.40$ mA/MHz.

Refer to applicable standard military drawing or NSC Table I for test conditions and I_C/I_{CC} limits.

AC Electrical Characteristics: See Section 2 for Waveforms

		54FCT/74FCT	74FCT		54	FCT	Units	Fig. No.
Symbol	Parameter	T _A = +25°C V _{CC} = 5.0V	T_A , $V_{CC}=Com$ $R_L=500\Omega$ $C_L=50$ pF		T_A , $V_{CC} = Mil$ $R_L = 500\Omega$ $C_L = 50 pF$			
		Тур	Min (Note 1)	Max	Min	Max		
t _{PLH}	Propagation Delay D _n to O _n	4.5	1.5	6.5	1.5	7.5	ns	2-8
t _{PZH}	Output Enable Time	6.0	1.5	8.0	1.5	10.5	ns	2-11
t _{PHZ}	Output Disable Time	5.0	1.5	7.0	1.5	8.0	ns	2-11

Note 1: Minimum limits are guaranteed but not tested on propagation delays.

Capacitance ($T_A = +25^{\circ}C$, f = 1.0 MHz)

Symbol	Parameter (Note)	Тур	Max	Units	Conditions
C _{IN}	Input Capacitance	6	10	pF	$V_{IN} = 0V$
C _{OUT}	Output Capacitance	8	12	pF	V _{OUT} = 0V

Note: This parameter is measured at characterization but not tested. $C_{\mbox{\scriptsize OUT}}$ for 74FCT only.